

SANYO

No.4317

2SJ307

P-Channel MOS Silicon FET

Very High-Speed
Switching Applications**Features**

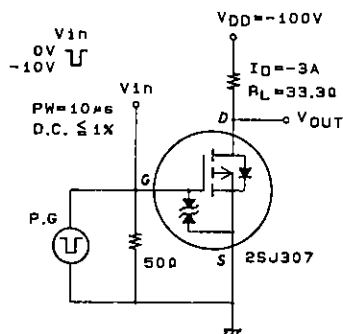
- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating mounting.

Absolute Maximum Ratings at Ta = 25°C

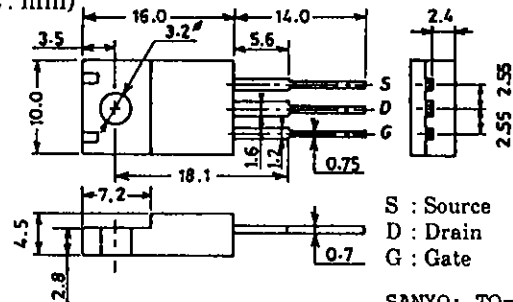
			unit
Drain to Source Voltage	V _{DSS}	-250	V
Gate to Source Voltage	V _{GSS}	±30	V
Drain Current(DC)	I _D	-6	A
Drain Current(Pulse)	I _{DP}	PW ≤ 10μs, duty cycle ≤ 1%	-24 A
Allowable Power Dissipation	P _D	2.0	W
		Tc = 25°C	30 W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} = 0	-250			V
G-S Breakdown Voltage	V _{(BR)GSS}	I _G = ±100μA, V _{DS} = 0	±30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -250V, V _{GS} = 0			-100	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±25V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -10V, I _D = -1mA	-1.5		-2.5	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -10V, I _D = -3A	3	5		S
Static Drain to Source on State Resistance	R _{DS(on)}	I _D = -3A, V _{GS} = -10V		0.75	1.0	Ω
Input Capacitance	C _{iss}	V _{DS} = -20V, f = 1MHz		1250		pF
Output Capacitance	C _{oss}	V _{DS} = -20V, f = 1MHz		235		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -20V, f = 1MHz		105		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		24		ns
Rise Time	t _r	∕		37		ns
Turn-OFF Delay Time	t _{d(off)}	∕		155		ns
Fall Time	t _f	∕		130		ns
Diode Forward Voltage	V _{SD}	I _S = -6A, V _{GS} = 0	-1.0	-1.5		V

Switching Time Test Circuit**Package Dimensions 2063**

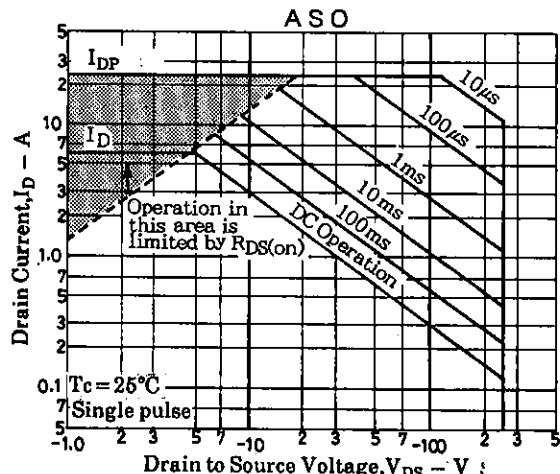
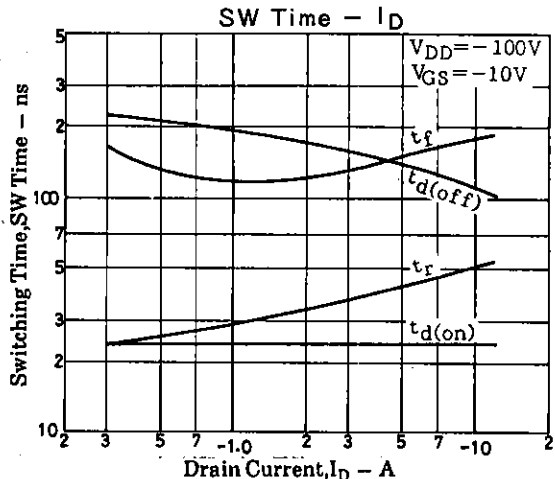
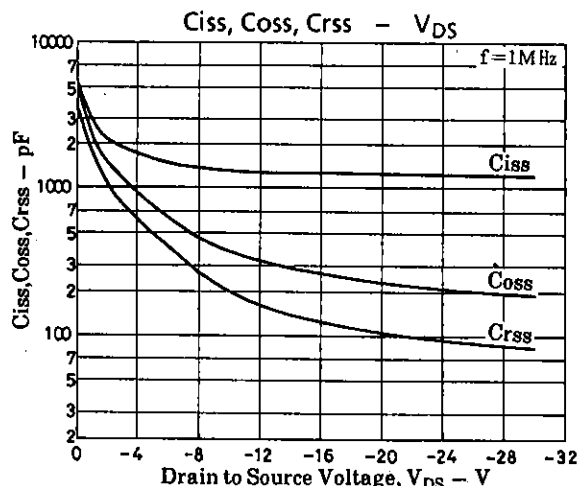
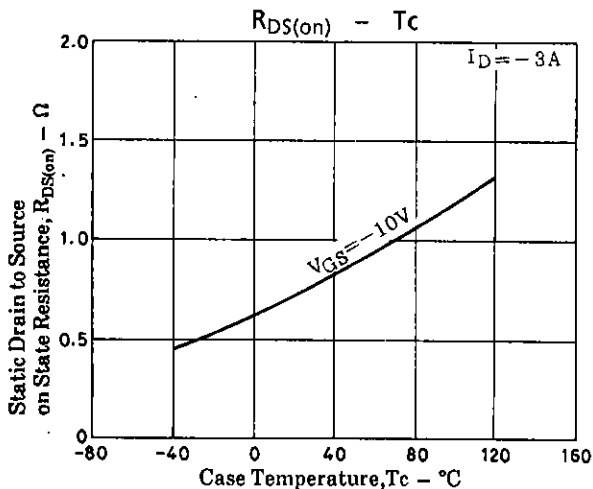
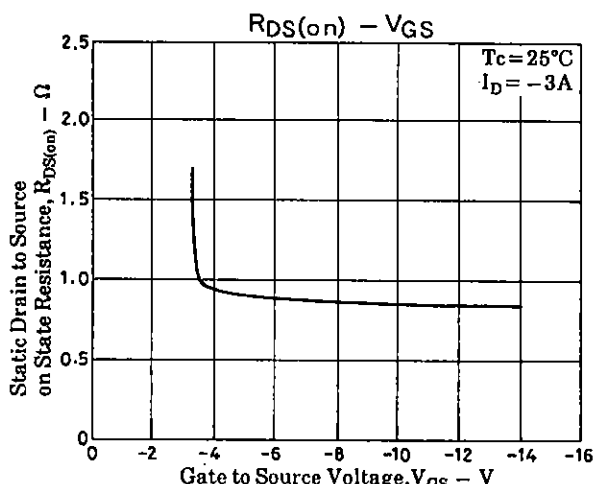
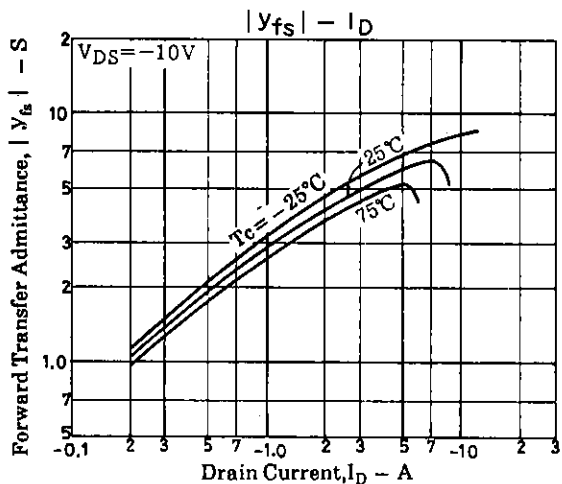
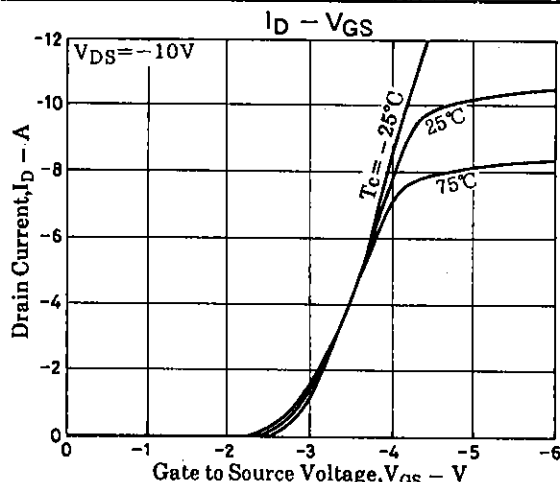
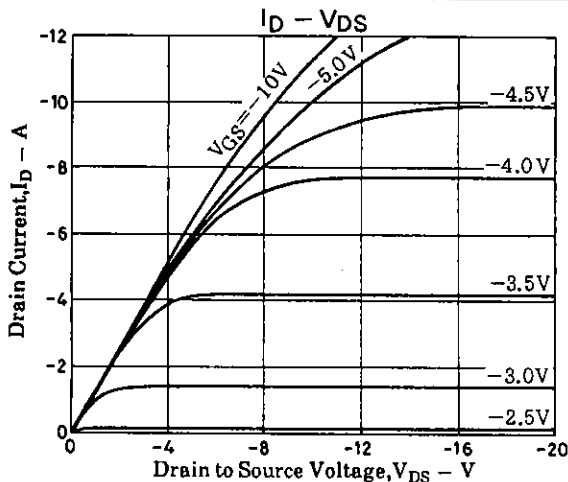
(unit: mm)

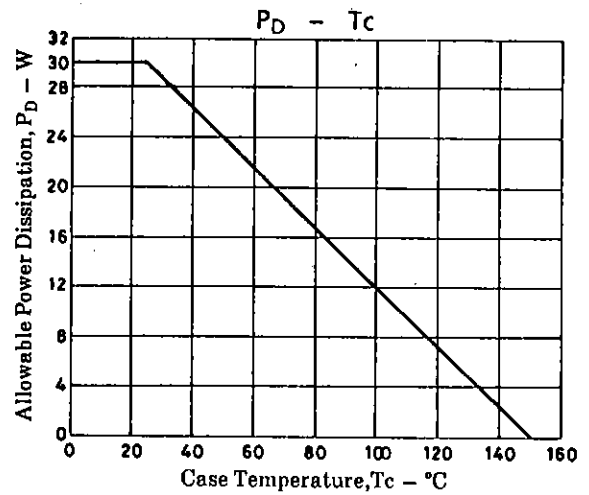
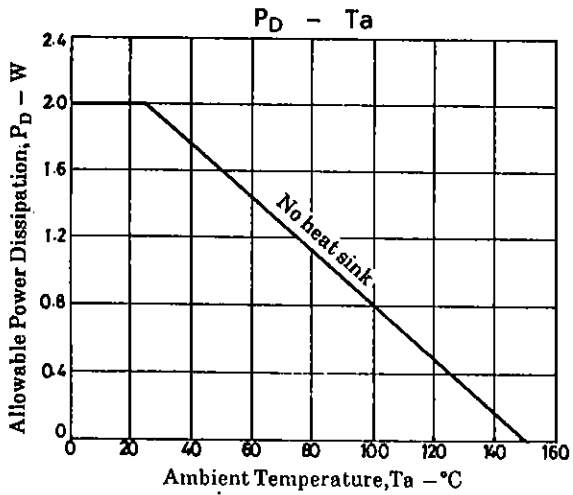
S : Source
D : Drain
G : Gate

SANYO: TO-220ML

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